

isc N-Channel MOSFET Transistor

APT20M18LVFR

FEATURES

- Drain Current –I_D= 100A@ T_C=25℃
- Drain Source Voltage-
 - : V_{DSS}=200V(Min)
- Static Drain-Source On-Resistance
 - : $R_{DS(on)} = 0.018 \Omega (Max)$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

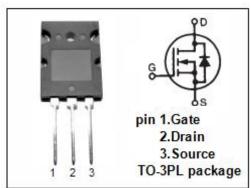
 Designed for use in switch mode power supplies and genera purpose applications.

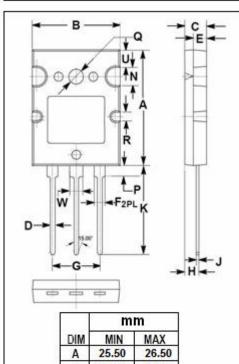
ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|---------|------------|
| V _{DSS} | Drain-Source Voltage | 200 | V |
| V _{GS} | Gate-Source Voltage-Continuous | ±30 | V |
| I _D | Drain Current-Continuous | 100 | Α |
| I _{DM} | Drain Current-Single Pluse | 400 | Α |
| P _D | Total Dissipation @T _C =25℃ | 625 | W |
| TJ | Max. Operating Junction Temperature | -55~150 | $^{\circ}$ |
| T _{stg} | Storage Temperature | -55~150 | $^{\circ}$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|--------------------------------------|------|------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 0.20 | °C/W |





| | mm | |
|-----|-------|-------|
| DIM | MIN | MAX |
| Α | 25.50 | 26.50 |
| В | 19.80 | 20.20 |
| C | 4.50 | 5.50 |
| D | 0.90 | 1.10 |
| E | 2.80 | 3.20 |
| F | 2.40 | 2.60 |
| G | 10.80 | 11.00 |
| H | 3.10 | 3.30 |
| J | 0.50 | 0.70 |
| K | 20.00 | 21.00 |
| N | 3.90 | 4.50 |
| Р | 2.40 | 2.60 |
| Q | 3.10 | 3.50 |
| R | 1.90 | 2.60 |
| U | 3.90 | 4.10 |
| W | 2.90 | 3.25 |



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|----------------------|---------------------------------|--|-----|-------------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D = 0.25mA | 200 | | V |
| V _{GS(th)} | Gate Threshold Voltage | V_{DS} = V_{GS} ; I_D = 2.5mA | 2 | 4 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =50A | | 0.018 | Ω |
| lgss | Gate-Body Leakage Current | V _{GS} = ±30V;V _{DS} = 0 | | ±100 | nA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 200V; V _{GS} = 0 V _{DS} = 160V; V _{GS} = 0@T _C =125°C | | 250 1000 | μА |
| V _{SD} | Forward On-Voltage | I _S =-100A; V _{GS} = 0 | | 1.3 | V |

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